

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	212238	light near emitting near (device or diode or element)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/21 15:19
L2	24370	(single-crystal\$4 near silicon) or (monocrystal\$4 near silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/21 15:20
L3	4067	(GaN or (gallium near nitride)) same buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/21 15:21
L4	2486	(GaN or (gallium near nitride)) same clad\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/21 15:23
L5	11810	etch\$3 same buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/21 15:25
L6	57727	dicing or cleaving	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/21 15:25
L7	9	I1 and I2 and I3 and I4 and I5 and I6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/21 15:26
L8	9	I1 and I2 and I3 and I4 and I6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/21 15:26
L9	15	I1 and I2 and I3 and I4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/21 15:26